BATOP optoelectronics

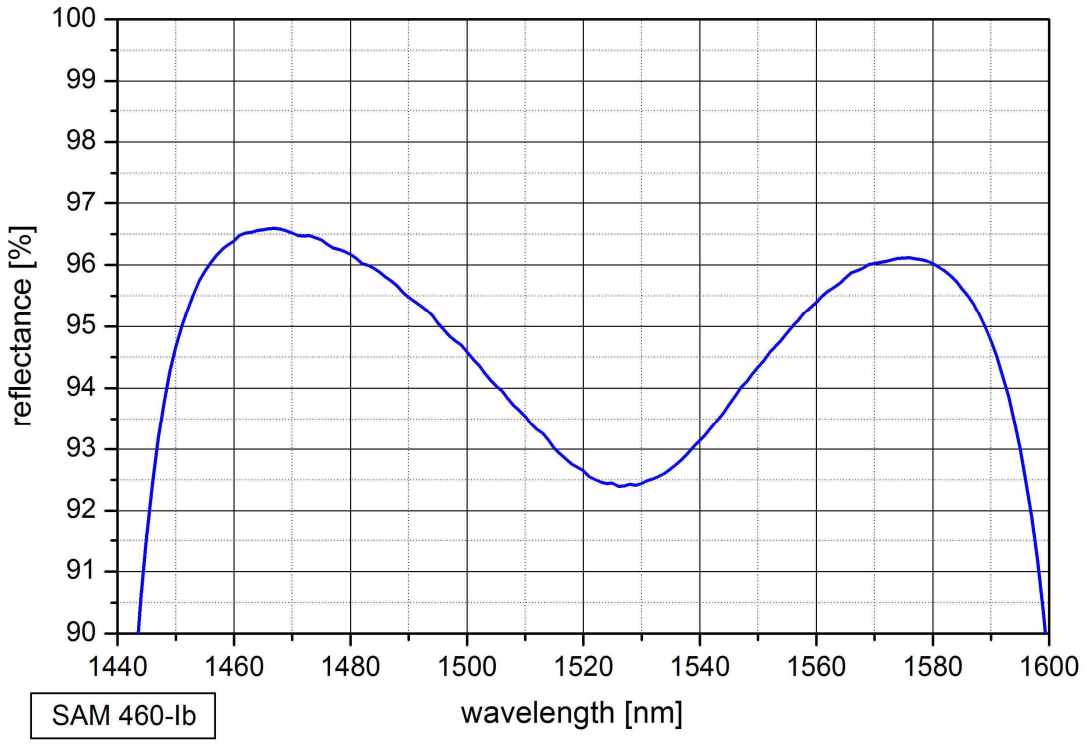
SAM™ Data Sheet SAM-1550-6-2ps-x, λ = 1550 nm

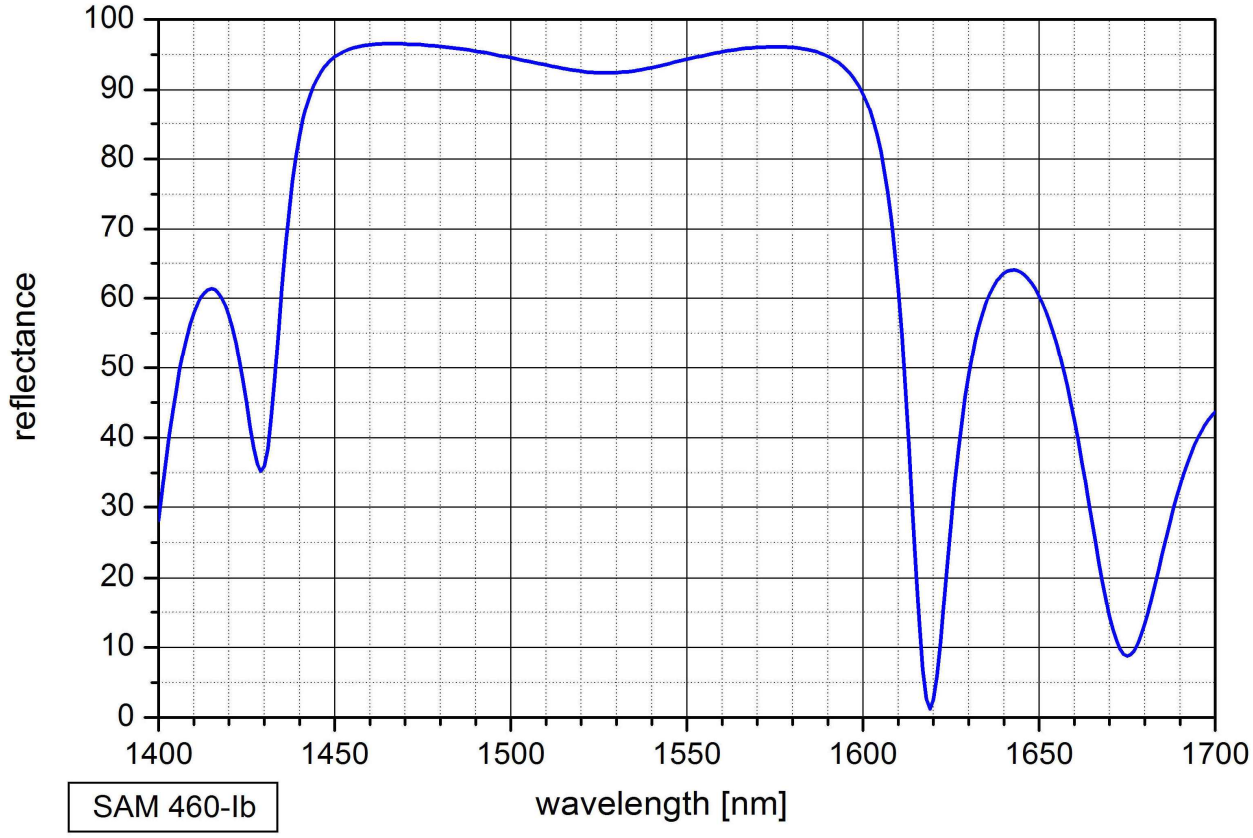
Laser wavelength	λ = 1550 nm
High reflection band	λ = 1460 .. 1580 nm
Absorbance	A_0 = 6 %
Modulation depth	ΔR = 3.6 %
Non-saturable loss	A_{ns} = 2.4 %
Saturation fluence	Φ_{sat} = 60 µJ/cm^2
Relaxation time constant	τ ~ 2 ps
Damage threshold	Φ = 1 mJ/cm^2
Chip area	4.0 mm x 4.0 mm; other dimensions on request
Chip thickness	450 µm
Protection	the SAM is protected with a dielectric front layer

Mounting option **x** denotes the type of mounting as follows:

x = 0	unmounted
x = 12.7 g	glued on a gold plated Cu-cylinder with 12.7 mm ∅
x = 25.4 g	glued on a gold plated Cu-cylinder with 25.4 mm ∅
x = 12.7 s	soldered on a gold plated Cu-cylinder with 12.7 mm ∅
x = 25.4 s	soldered on a gold plated Cu-cylinder with 25.4 mm ∅
x = 25.0 w	soldered on a water cooled Cu-cylinder with 25.4 mm ∅
x = FC	mounted on a 1 m monomode fiber cable with FC connector

Low intensity spectral reflectance




reflectance
100
90
80
70
60
50
40
30
20
10
0
1400
1450
1500
1550
1600
1650
1700
wavelength [nm]
SAM 460-Ib